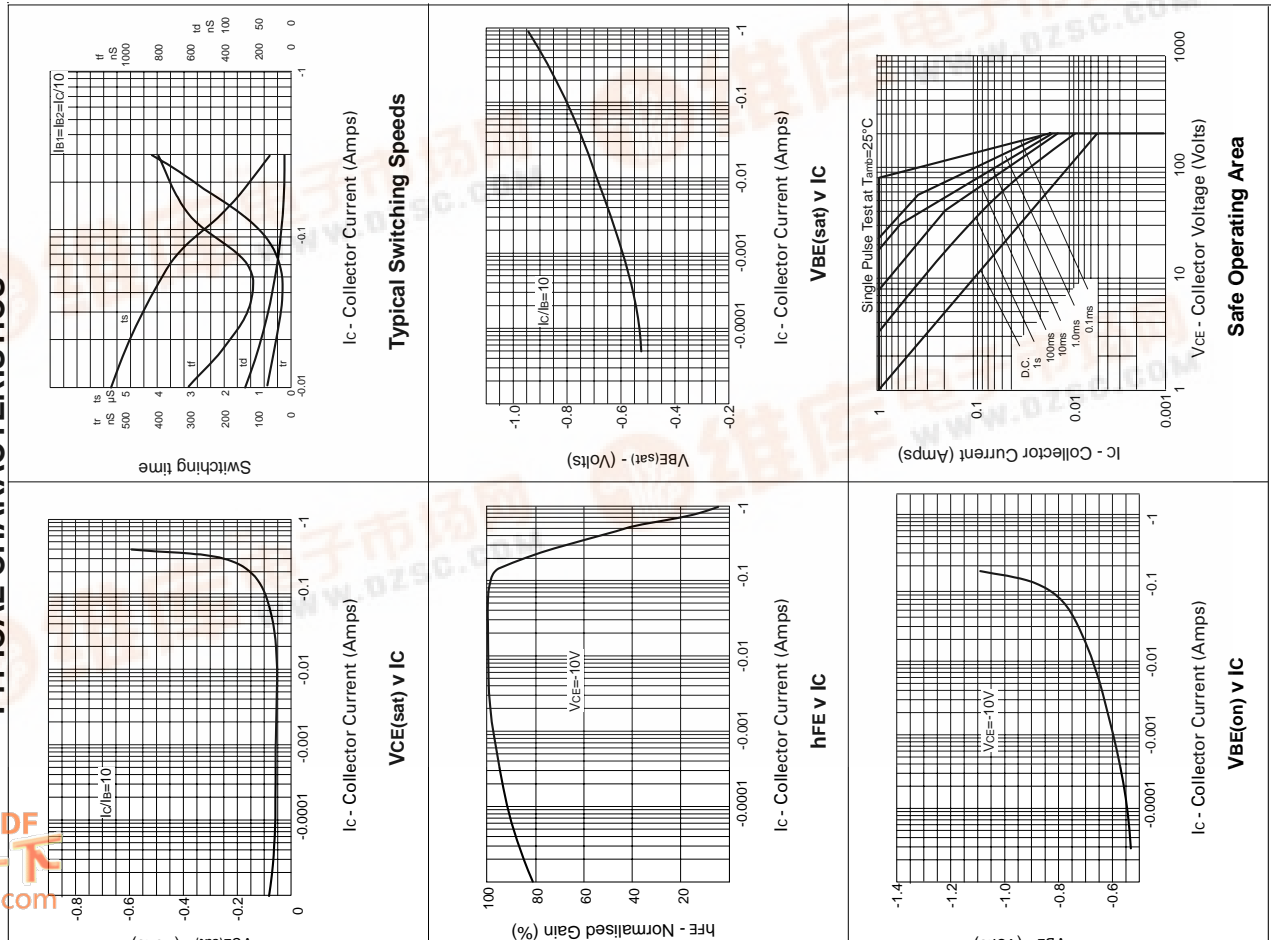




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TYPICAL CHARACTERISTICS

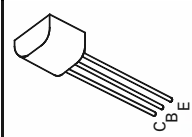


PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

ISSUE 1 – APRIL 94

FEATURES

- * 200 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 1 Watt



E-Line
TO92 Compatible

查询ZTX576供应商

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-200	V
Collector-Emitter Voltage	V _{CEO}	-200	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-2	A
Continuous Collector Current	I _C	-1	A
Power Dissipation at T _{amb} =25°C	P _{tot}	1	W
Operating and Storage Temperature Range	T _J ; T _{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-200			V	I _C = -100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-200			V	I _C = -10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5			V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}			-0.1	μA	V _{CB} = -160V
Emitter Cut-Off Current	I _{EBO}			-0.1	μA	V _{EB} = -4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.3	V	I _C = -100mA, I _B = -10mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1	V	I _C = -100mA, I _B = -10mA*
Base-Emitter Turn-on Voltage	V _{BE(on)}			-1	V	I _C = -100mA, V _{CE} = -10V*
Static Forward Current Transfer Ratio	h _{FE}	50		300		I _C = -10mA, V _{CE} = -10V* I _C = -300mA, V _{CE} = -10V*
Transition Frequency	f _T	100			MHz	I _C = -50mA, V _{CE} = -10V f = 100MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

捷多邦, 专业PCB打样工厂, 24小时加急出货

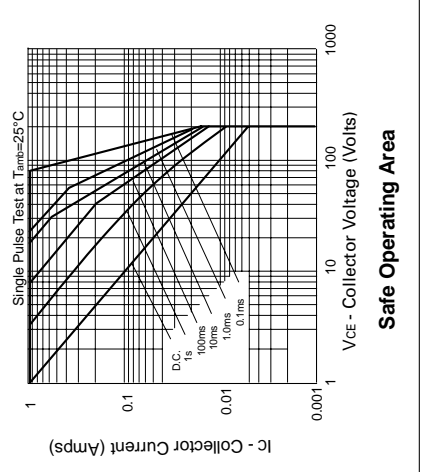
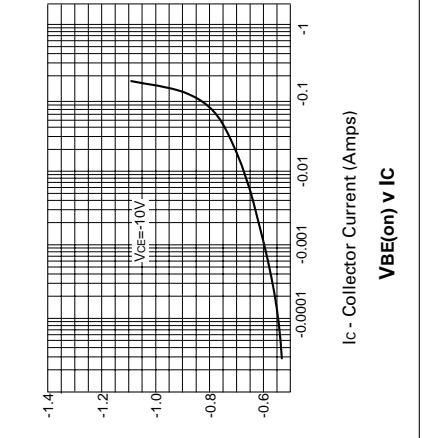
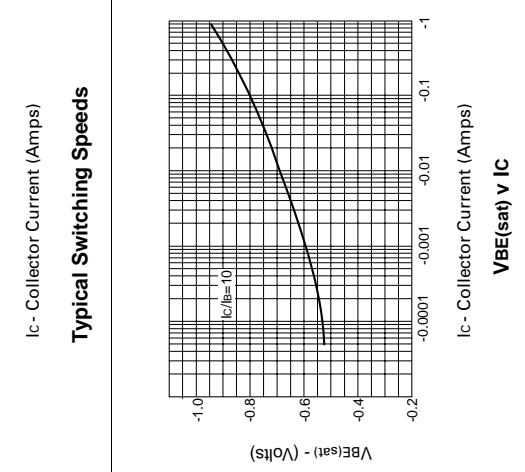
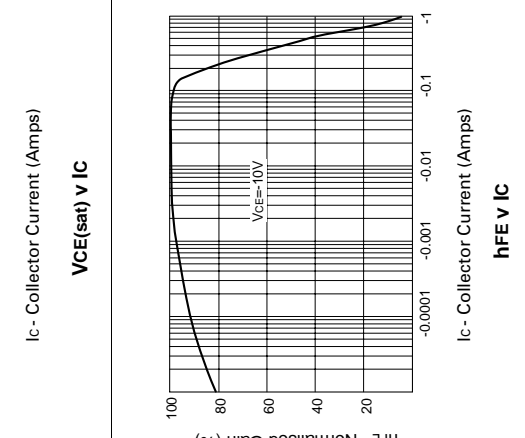
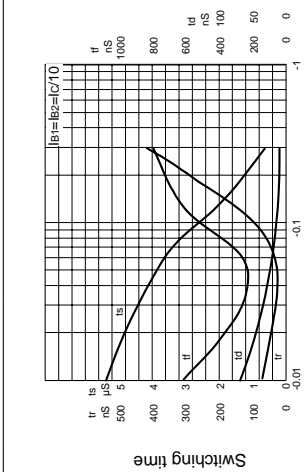
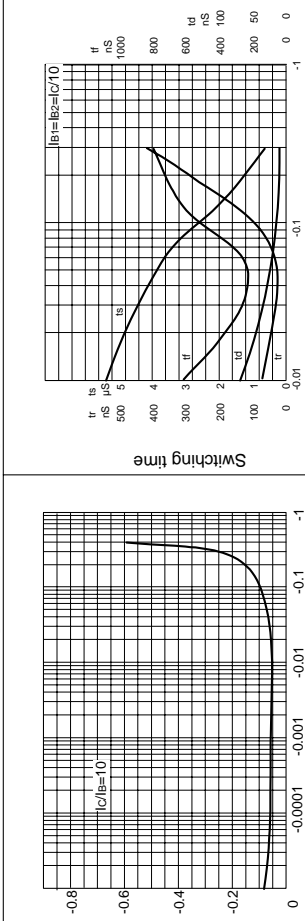
PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

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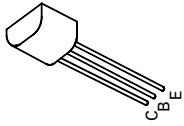
ISSUE 1 - APRIL 94

TYPICAL CHARACTERISTICS



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